

REMARKS

The Final Office Action of February 12, 2008 was received and carefully reviewed. By way of the present Amendment and with the filing of a Request for Continued Examination, claims 87, 88, 90, 91, 123, 124, 126, 127, 137, and 143 have been amended to further define the invention and to correct minor typographical errors, and claims 73-86, 89, 93-116, 125, 129-136, 138-141, 144-148, and 150-155 have been canceled without prejudice or disclaimer. Accordingly, claims 87, 88, 90-92, 123, 124, 126-128, 137, 143, and 149 are currently pending in the instant application.

Applicants respectfully assert that support for the features recited by amended independent claims 87 and 123 may be found in the original specification, for example, with regard to the fifth and sixth disclosed embodiments of the original specification. Accordingly, Applicants respectfully assert that no new matter is introduced by way of the present Amendment.

On pages 2 to 21 of the Final Office Action, claims 73-116, 123-141, and 143-155 stand rejected under 35 U.S.C. § 103(a) as being unpatentable over Zhang et al. (US 5,563,426). Applicants respectfully traverse these rejections for at least the following reasons.

Independent claims 87 and 123, as amended, both recite a semiconductor device including, in part, first and second thin film transistors having crystalline semiconductor islands including nickel, wherein “a concentration of said nickel in said crystalline semiconductor island of said first thin film transistor is smaller than that of said nickel in said crystalline semiconductor island of said second thin film transistor.” In direct contrast to Applicants’ claimed invention, Zhang et al. is completely silent with regard to formation of thin film transistors having differing nickel concentrations. Specifically, Zhang et al. repeatedly discloses formation of a crystalline semiconductor region subdivided into individual regions each having identical concentrations of nickel. Thus, Applicants respectfully assert that Zhang et al. fails to teach or suggest a semiconductor device including, in part, first and second thin film transistors having crystalline semiconductor islands including nickel, wherein “a concentration of said nickel in said crystalline semiconductor island of said first thin film transistor is smaller than that of said nickel in said crystalline semiconductor island of said second thin film transistor,” as required by amended

independent claims 87 and 123, and hence dependent claims 88, 90-92, 124, 126-128, 137, 143, and 149.

For at least the reasons presented above, Applicants respectfully assert that the Final Office Action fails to establish a *prima facie* case of obviousness with regard to at least independent claims 87 and 123, and hence dependent claims 88, 90-92, 124, 126-128, 137, 143, and 149. Applicants respectfully request that the rejection of all pending claims under 35 U.S.C. § 103(a) in view of Zhang et al. be withdrawn.

Applicants respectfully assert that the present Amendment places the above-referenced application in immediate condition for allowance. Thus, Applicants respectfully request that the prior art rejection of record be reconsidered and withdrawn by the Examiner, that all pending claims be indicated as allowable, and that the application be passed to issue.

If a conference would expedite prosecution of the instant application, the Examiner is hereby invited to telephone the undersigned to arrange such a conference.

Respectfully submitted,
NIXON PEABODY LLP

\David B. Hardy, Reg. No. 47,362\
David B. Hardy
Registration No. 47,362

Date: May 12, 2008

CUSTOMER NO. 22204
NIXON PEABODY LLP
Suite 900, 401 9th Street, N.W.
Washington, D.C. 20004-2128
(202) 585-8000